

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 05-047665

(43)Date of publication of application : 26.02.1993

(51)Int.Cl.

H01L 21/205

(21)Application number : 03-201027

(71)Applicant : FUJITSU LTD

(22)Date of filing : 12.08.1991

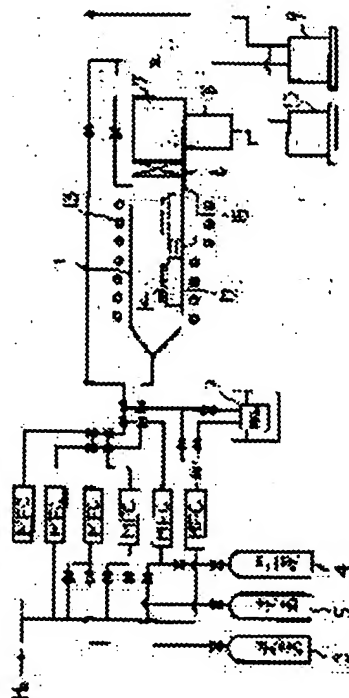
(72)Inventor : NAKAI KENYA

(54) VAPOR GROWTH METHOD

(57)Abstract:

PURPOSE: To prevent carbon contamination when organic metal material gas is used by introducing gas made of hydroxide into a reaction tube before material gas of silicon is introduced when organic compound is used as the material gas and an Si-Ge mixed crystal is grown by an atomic layer epitaxy method.

CONSTITUTION: A silicon substrate 14 is placed on a susceptor 12 in a reaction tube 1, the substrate 14 is heated to 900° C, and a spontaneous oxide film on the surface is removed. A temperature of the susceptor 12 is set to 390° C, diethylgermanium (DEGe) is introduced into the tube 1, and a Ge layer is grown on the substrate 14. The introduction of the DEGe is stopped, the DEGe in the tube 1 is discharged, the temperature of the susceptor 12 is set to 450° C, and AsH₃ is introduced. After the AsH₃ in the tube 1 is discharged, the temperature of the susceptor 12 is raised to 530° C, Si₂H₆ is introduced, and an Si layer is grown on the substrate 14. Thereafter, the above steps are similarly repeated to grow an Si-Ge crystalline layer.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]